

K. Memory (Design & Process Technology) 분과

2020년 2월 13일(목), 10:45-12:30 / Room G (스페이드 II+III, 6층)

■ [TG2-K] Emerging Memory I

좌장: 강명곤 교수 (한국교통대학교), 백승재 교수 (한경대학교)

TG2-K-1 10:45-11:15	<p>[초청]</p> <p>Future Outlook and Applications of Ferroelectric-based Memory Devices</p> <p>Jae-Gil Lee, Dong-Ik Suh, and Seho Lee <i>SK Hynix Inc.</i></p>
TG2-K-2 11:15-11:45	<p>[초청]</p> <p>Ferroelectric $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ Thin Films</p> <p>Si Joon Kim <i>Department of Electrical and Electronics Engineering, Kangwon National University</i></p>
TG2-K-3 11:45-12:00	<p>Highly Linear and Symmetric Synaptic Function of a Memristive Device for Spiking Neural Network System</p> <p>Jin Joo Ryu^{1,2}, Kanghyeok Jeon¹, Min Kyu Yang³, Chunjoong Kim², and Gun Hwan Kim¹ ¹<i>Division of Advanced Materials, KRICT</i>, ²<i>Department of Materials Science and Engineering, Chungnam National University</i>, ³<i>Division of IT Convergence Engineering, Sahmyook University</i></p>
TG2-K-4 12:00-12:15	<p>The Origin of Incremental Step Pulse Programming (ISPP) Slope Degradation in NAND Flash Memory</p> <p>Kihoon Nam, Chanyang Park, Jun-Sik Yoon, Hyun-Dong Jang, and Rock-Hyun Baek <i>Department of Electrical Engineering, POSTECH</i></p>
TG2-K-5 12:15-12:30	<p>Effect of Interface Roughness on Program/Erase Efficiency for 3D Vertical NAND Flash Memory Applications</p> <p>Yongjin Cho, Hyeongwan Oh, Gilsang Yoon, Jaeseok Jin, Donghyun Go, Jounghun Park, and Jeongsoo Lee <i>Department of Electrical Engineering, POSTECH</i></p>